

- On page 1, please replace the text at ll. 5 – 16 with the following:

CROSS REFERENCE TO RELATED APPLICATIONS

The present application claims priority to, and is a divisional of parent application serial no. 10/298,916 filed November 18, 2002, titled FIELD EFFECT TRANSISTOR PULL-UP/LOAD ELEMENT now U.S. Patent No. 6,724,024 which parent application is in turn a continuation of serial no. 10/028,085 entitled “IMPROVED NEGATIVE DIFFERENTIAL RESISTANCE FIELD EFFECT TRANSISTOR (NDR-FET) & CIRCUITS USING THE SAME” which was filed December 21, 2001, now U.S. Patent No. 6,559,470; both such applications are hereby incorporated by reference as if fully set forth herein.

~~The present application is a continuation in part of each of the following applications, all of which were filed June 22, 2000 and are hereby incorporated by reference as if fully set forth herein:~~

~~—Serial no. 09/603,101 entitled “A CMOS PROCESS COMPATIBLE, TUNABLE NDR (NEGATIVE DIFFERENTIAL RESISTANCE) DEVICE AND METHOD OF OPERATING SAME”; and~~

~~—Serial No. 09/603,102 entitled “CHARGE TRAPPING DEVICE AND METHOD FOR IMPLEMENTING A TRANSISTOR HAVING A NEGATIVE DIFFERENTIAL RESISTANCE MODE”; and~~

~~—Serial No. 09/602,658 entitled “CMOS COMPATIBLE PROCESS FOR MAKING A TUNABLE NEGATIVE DIFFERENTIAL RESISTANCE (NDR) DEVICE.”~~

- Please replace the following text beginning on page 2, ll. 9:

-- BACKGROUND OF THE INVENTION

A new type of CMOS compatible, NDR capable FET is ~~described in the aforementioned applications to *King et al.* referenced above~~ disclosed in the following *King et al.* applications: Serial no. 09/603,101 entitled “A CMOS-PROCESS COMPATIBLE, TUNABLE NDR (NEGATIVE DIFFERENTIAL RESISTANCE) DEVICE AND METHOD OF OPERATING SAME”; and Serial No. 09/603,102 entitled “CHARGE TRAPPING DEVICE AND METHOD FOR IMPLEMENTING A TRANSISTOR HAVING A NEGATIVE DIFFERENTIAL RESISTANCE MODE”; and Serial No. 09/602,658 entitled “CMOS COMPATIBLE PROCESS FOR MAKING A TUNABLE NEGATIVE DIFFERENTIAL RESISTANCE (NDR) DEVICE all of which were filed June 22, 2000 and which are hereby incorporated by reference as if fully set forth herein. The advantages of such device are well set out in such materials, and are not repeated here. --

- Please replace the Abstract with the following: